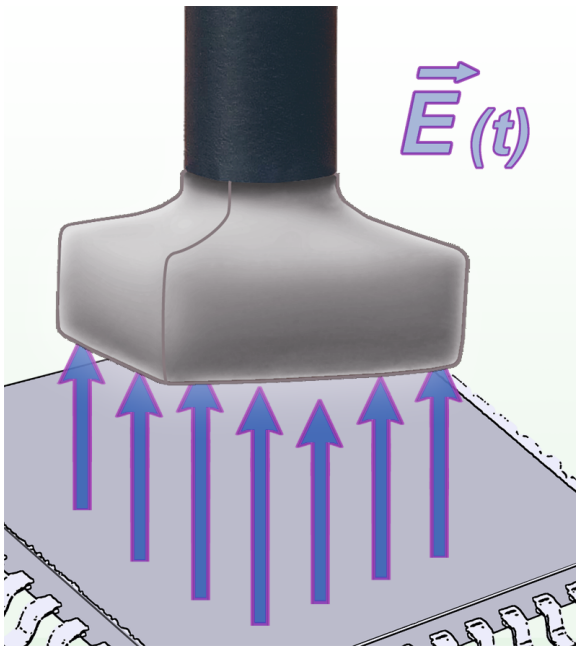




Short description

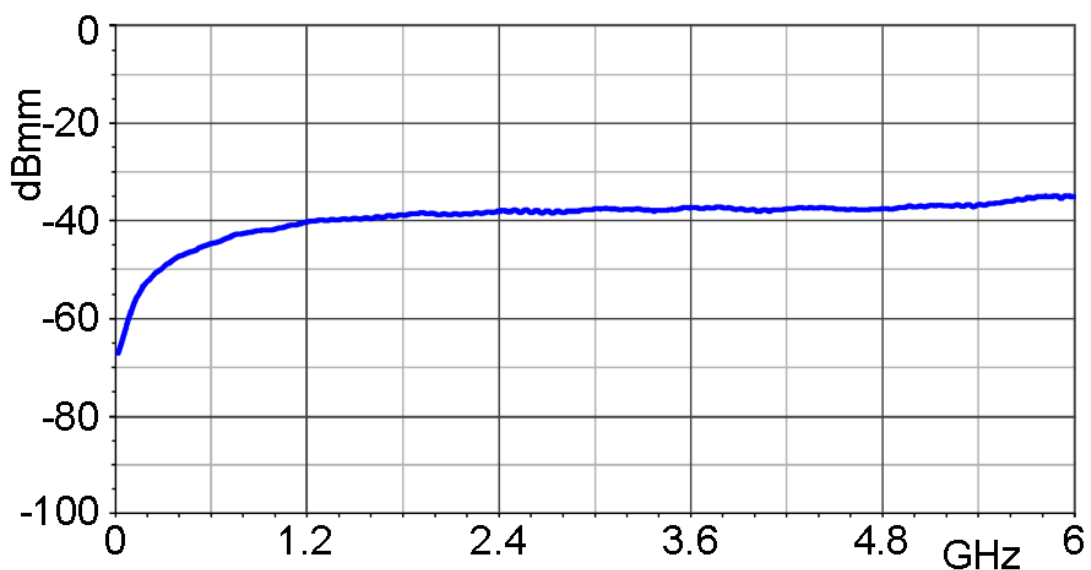
这种近场探头可以检测受测对象 (IC) 耦合产生的电场。探头的侧面采用屏障设计，所以侧面作用的电场不影响测量结果。这种近场探头的灵敏度允许在0.5到10mm的距离检测集成电路及其他电子模块的电场。

The XF-E 09s is a passive near-field probe. In principle it has the same structure as the XF-E 04s probe. To measure, the E-field probe is positioned above or onto components and printed circuit boards. It has a current attenuating sheath and, therefore, its upper half is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The E-field probe has an internal terminating resistance.

Technical parameters

频率范围	30 MHz ... 6 GHz
探头尺寸	$\approx (10 \times 10)$ mm
输出接口	SMA, female, jack

频率特性 [dB μ V] / [dB μ V/mm]

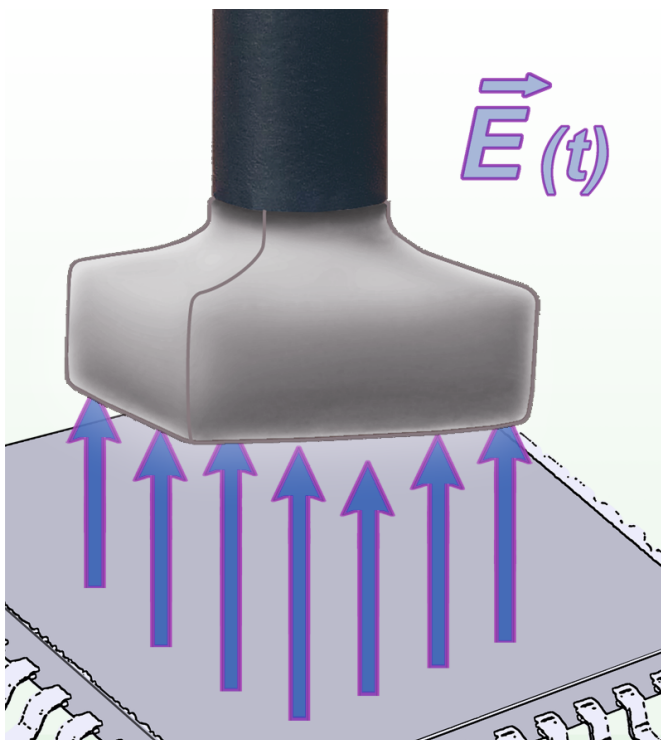
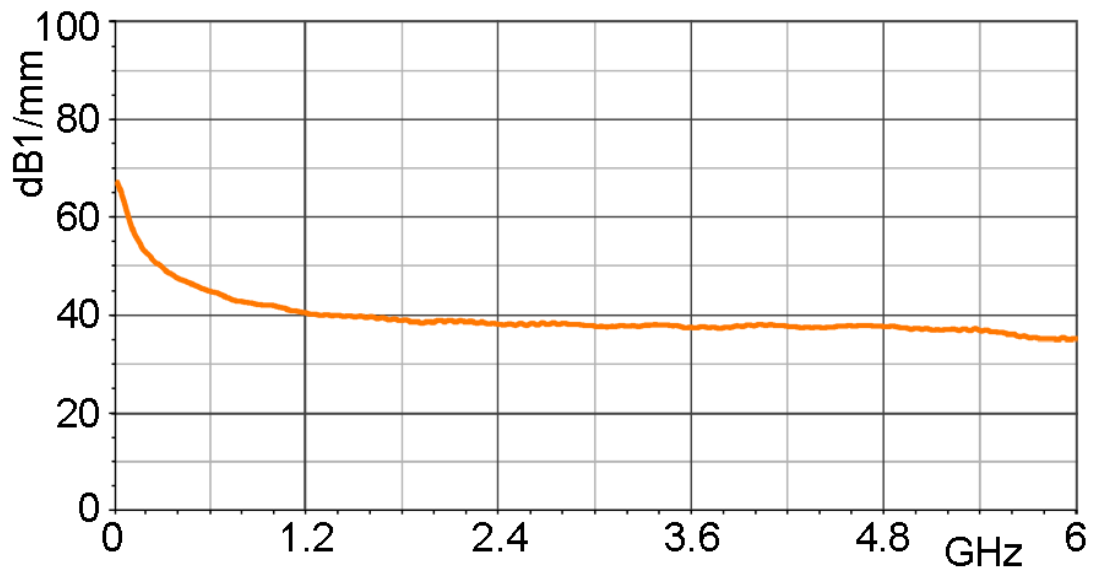


XF-E 09s

电场探头 (30MHz-6GHz)

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电场校正曲线 [dB μ V/mm] / [dB μ V]



XF-E 09s

电场探头 (30MHz-6GHz)

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EMV-Technik

Probe head

